# Characterization of RD53A pixel modules with passive CMOS sensors







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CMS market survey submission by LFoundry:

150 μm thickness

built using CMOS technology

 $25 \times 100 \ \mu m^2$  pixel size

IV measurements Phase 2 requirements: 0.75  $\mu$ A per cm<sup>2</sup> at V<sub>dep</sub> + 50 V Breakdown > 300 V

→ Leakage current and

is also well behaved.

breakdown voltage in

→ The first batch of bare sensors showed a very high leakage current  $(V_{dep} = 40 V).$ 

backside implant doping.

- compliance with the Phase-2 specifications. → Fixed by increasing the → The IV after irradiation
  - DC 25x100, high doping, on chip, T = 20 degrees  $10^{-1}$ DC 50x50, high doping, on chip, T = -25 degrees <sup>2</sup> E 10<sup>−2</sup> dose =  $5 \times 10^{15}$  neq.cm<sup>2</sup> AC 50x50, low doping -- DC 25x100, low doping ⊕ 10<sup>-3</sup> -- AC 50x50, low doping DC 50x50, low doping  $10^{-4}$ ensity 10<sup>-5</sup> Max current at  $V_{dep}+50$  V ₹ 10<sup>-6</sup>  $3 10^{-7}$  $10^{-8}$ 250 300 350 150 200 Bias voltage (in V)

 $n^+$  in p

Efficiency

CMOS sensors and stitching

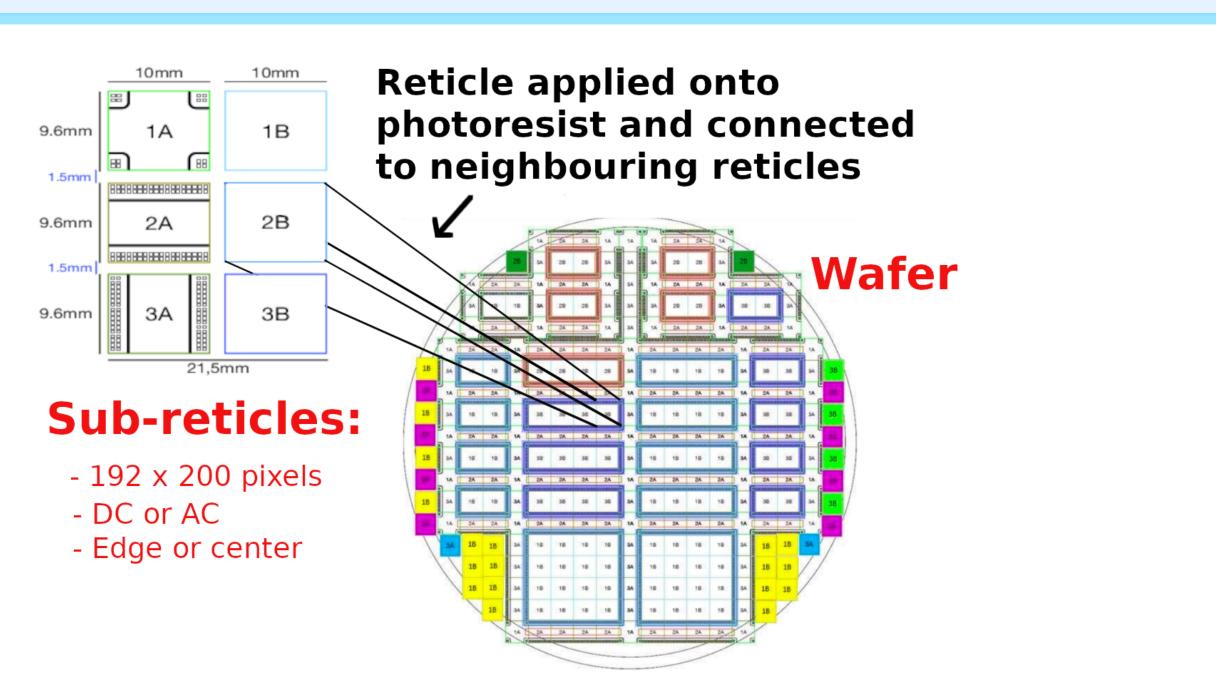
The characterized samples are passive planar n-in-p sensors for hybrid modules built in CMOS technology using the 150 nm production line of LFoundry and the stitching process.

Advantages of CMOS sensors:

- → Reuse of CMOS libraries from the industry
- → Large throughput and low cost
- → Implementation of small on-pixel features

LFoundry on-sensor features:

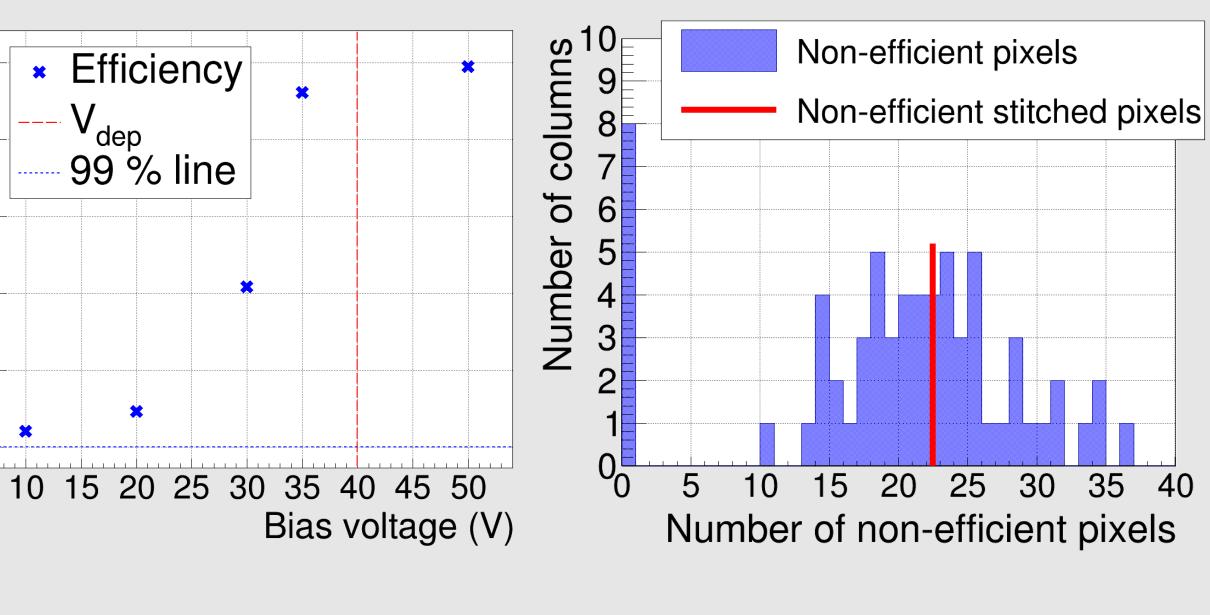
- → Metal layers on the sensor for signal redistribution
- → DC or AC-coupled sensors
- → Low and high resistivity polysilicon layers



Phase 2 requirement: 99 % efficiency at  $V_{dep} + 50 V$ 

The efficiency is the probability of detecting a hit on the sensor within 500 µm of each reconstructed hit. Testbeam measurements give the following results.

- → The efficiency requirement is satisfied before the depletion voltage.
- → The stitching process does not reduce the efficiency.

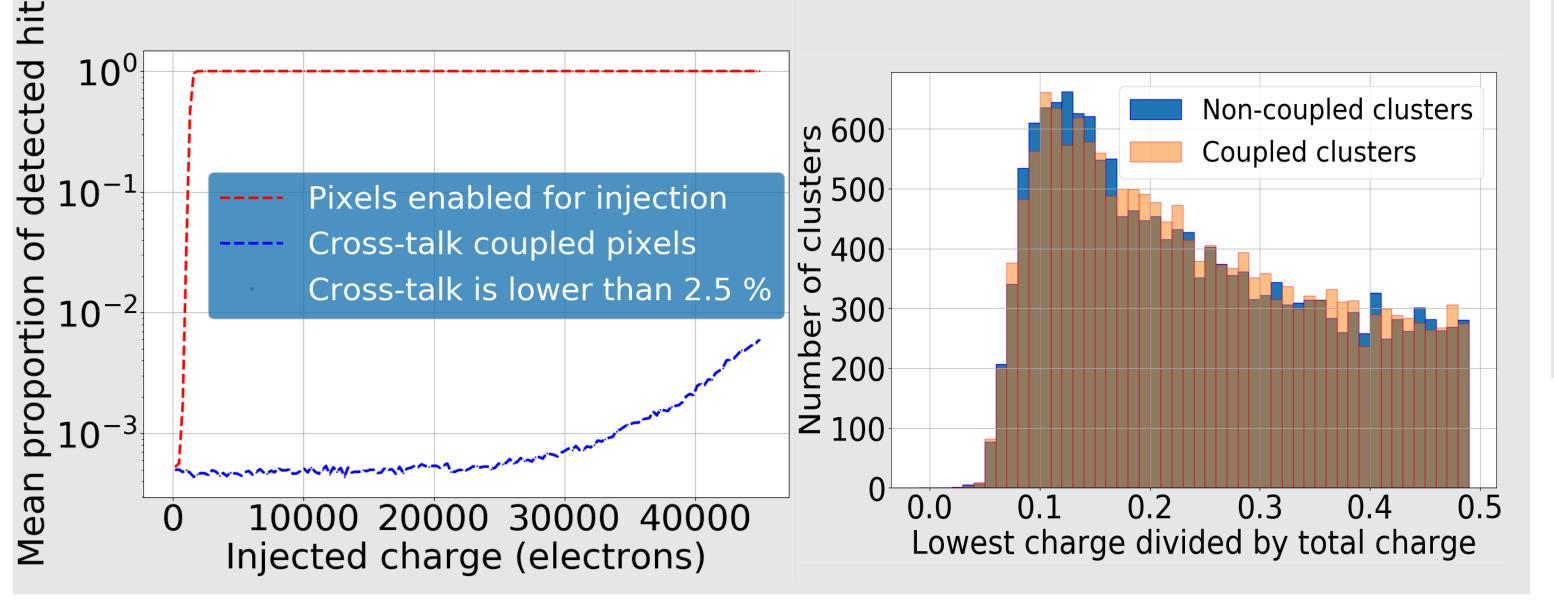


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## Crosstalk

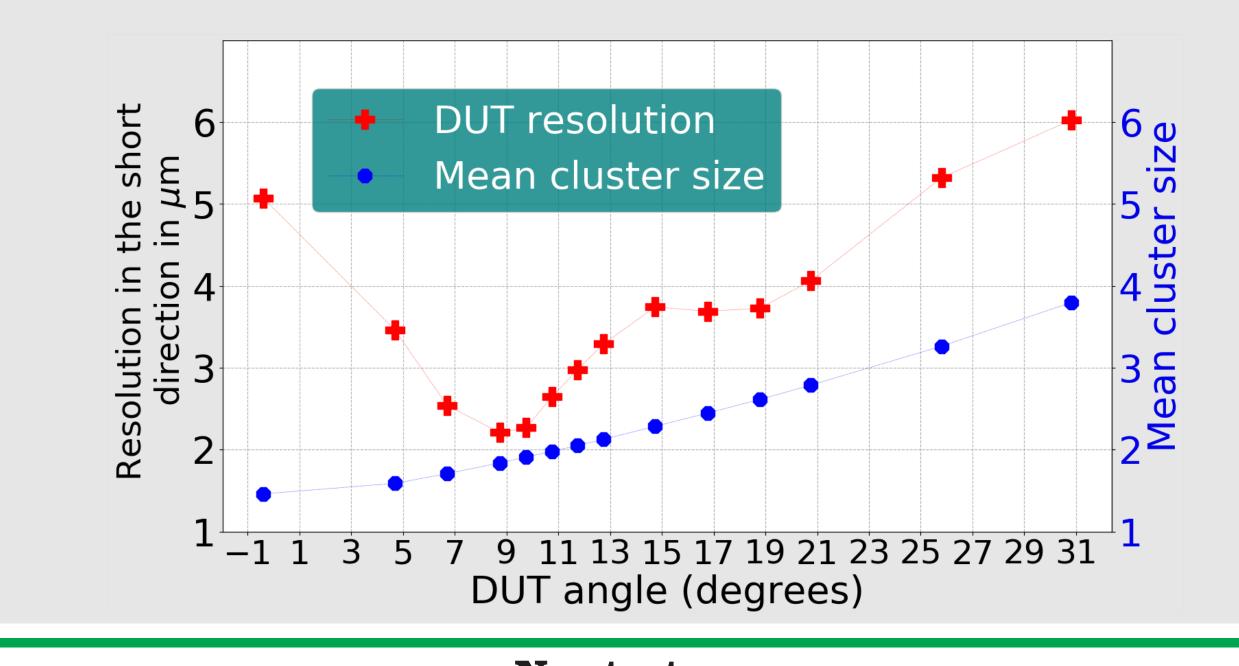
Capacitive coupling between neighbouring pixels leads to spurious hits and can deteriorate the sensor's resolution.

- RD53A of a known charge the crosssmaller talk than 3%.
- → Injection through the → The ratio of the lowest charge over the total charge for 2-pixel clusters showed cross-talk is smaller than 6%.



### Resolution

Minimal resolution of  $2.2 \mu m$  in the  $25 \mu m$  direction around 9.5 degrees. The CMS tracker has a Lorentz angle of 11.5 degrees.



#### Next steps

- Modules irradiated up to  $10^{16}$  neq.cm $^{-2}$  to be tested - New sensor submission expected this year

#### Charge collection

→ Time-over-threshold distribution from DESY testbeam runs.

0.998

0.996

0.994

0.992

0.99

→ Charge calibration of the RD53A using fluorescent X-ray sources.

Full charge collection of approximately 12000 electrons is reached for a bias voltage of 40 V.

